



SOT-23 Plastic-Encapsulated Diodes

BAS16LT1 SWITCHING DIODE

FEATURES

Power dissipation

$$P_D: 225 \text{ mW (} T_{amb}=25^\circ\text{C)}$$

Forward Current

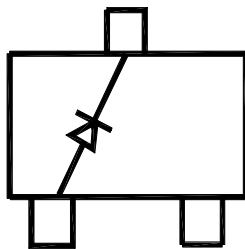
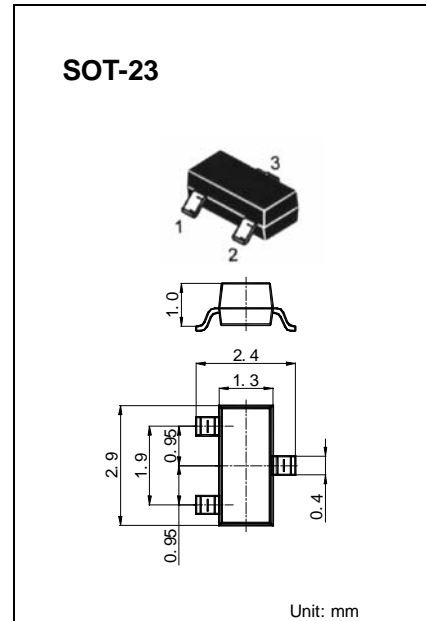
$$I_F: 200 \text{ mA}$$

Reverse Voltage

$$V_R: 75 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



Marking A6

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R=75\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		2	pF
Reverse recovery time	t_{rr}			6	nS